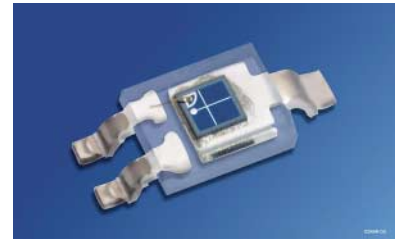


NPN-Silizium-Fototransistor Silicon NPN Phototransistor

SFH 3400



Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 460 nm bis 1080 nm
- Hohe Linearität
- SMT-Bauform ohne Basisanschluß, geeignet für Vapor Phase-Löten und IR-Reflow-Löten (JEDEC level 4)
- Nur gegurtet lieferbar

Anwendungen

- Umgebungslicht-Detektor
- Lichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 460 nm to 1080 nm
- High linearity
- SMT package without base connection, suitable for vapor phase and IR reflow soldering (JEDEC level 4)
- Available only on tape and reel

Applications

- Ambient light detector
- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 3400	Q62702-P1796	Klares Epoxy-Gießharz, Kollektorkennzeichnung: breiter Anschluß Transparent epoxy resin, collector marking: broad lead
SFH 3400-2/3	Q62702-P3605	

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	– 40 ... + 100	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	20	V
Kollektor-Emitterspannung, $t < 120$ s Collector-emitter voltage	V_{CE}	70	V
Kollektorstrom Collector current	I_C	50	mA
Kollektorspitzenstrom, $\tau < 10$ μ s Collector surge current	I_{CS}	100	mA
Emitter-Kollektorspannung Emitter-collector voltage	V_{EC}	7	V
Verlustleistung, $T_A = 25$ °C Total power dissipation	P_{tot}	120	mW
Wärmewiderstand für Montage auf PC-Board Thermal resistance for mounting on pcb	R_{thJA}	450	K/W

Kennwerte ($T_A = 25\text{ °C}$, $\lambda = 950\text{ nm}$)

Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	460 ... 1080	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.55	mm ²
Abmessungen der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	1×1	mm × mm
Halbwinkel Half angle	φ	± 60	Grad deg.
Kapazität, $V_{\text{CE}} = 5\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_{CE}	10	pF
Dunkelstrom Dark current $V_{\text{CE}} = 10\text{ V}$, $E = 0$	I_{CEO}	3 (≤ 200)	nA

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.

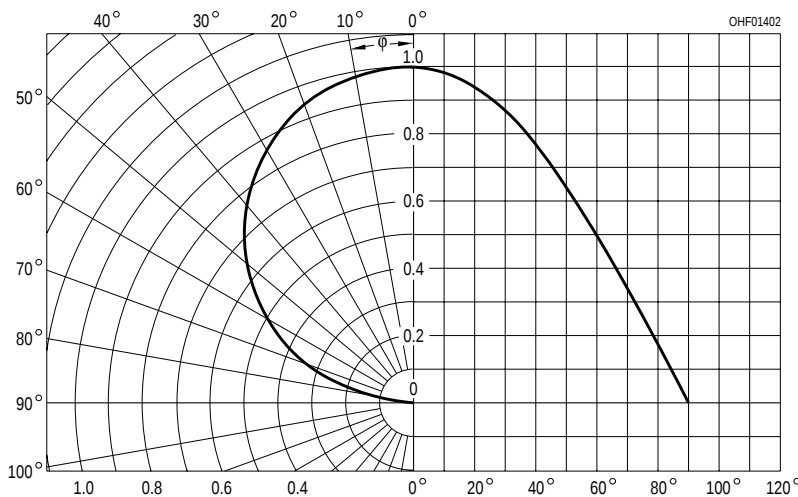
The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

Bezeichnung Parameter	Symbol Symbol	Wert Value			Einheit Unit
		-1	-2	-3	
Fotostrom, $\lambda = 950 \text{ nm}$ Photocurrent $E_e = 0.1 \text{ mW/cm}^2$, $V_{CE} = 5 \text{ V}$ $E_v = 1000 \text{ lx}$, Normlicht A/ standard light A, $V_{CE} = 5 \text{ V}$	I_{PCE} I_{PCE}	63 ... 125 1.65	100 ... 200 2.6	160 ... 320 4.2	μA mA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 1 \text{ k}\Omega$	t_r , t_f	16	24	34	μs
Kollektor-Emitter- Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}^{1)} \times 0.3$, $E_e = 0.1 \text{ mW/cm}^2$	V_{CEsat}	170	170	170	mV

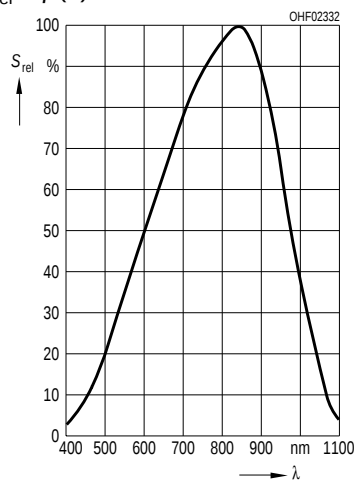
1) I_{PCEmin} ist der minimale Fotostrom der jeweiligen Gruppe.

1) I_{PCEmin} is the min. photocurrent of the specified group.

Directional Characteristics $S_{rel} = f(\varphi)$

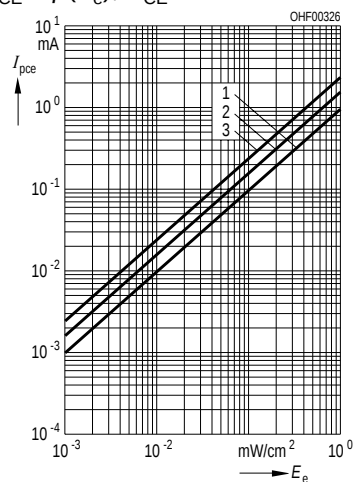


Rel. Spectral Sensitivity,
 $S_{\text{rel}} = f(\lambda)$



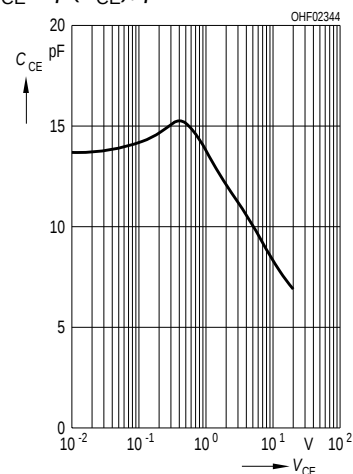
Photocurrent

$$I_{\text{PCE}} = f(E_e), V_{\text{CE}} = 5 \text{ V}$$

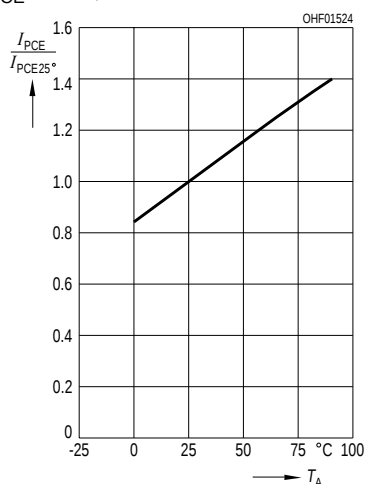


Collector-Emitter Capacitance

$$C_{\text{CE}} = f(V_{\text{CE}}), f = 1 \text{ MHz}$$

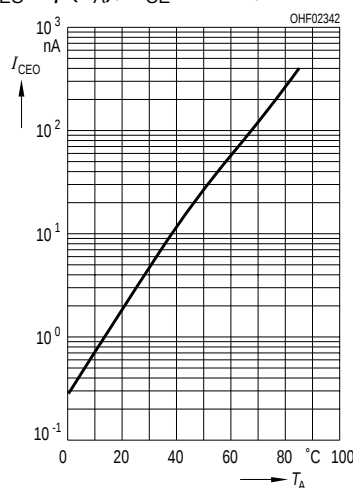


Photocurrent $I_{\text{PCE}} = f(T_A)$,
 $V_{\text{CE}} = 5 \text{ V}$, normalized to 25 °C



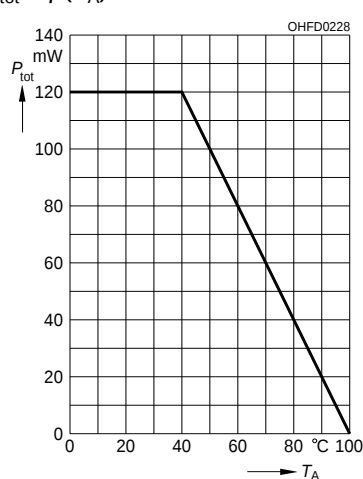
Dark Current

$$I_{\text{CEO}} = f(T_A), V_{\text{CE}} = 10 \text{ V}, E = 0$$



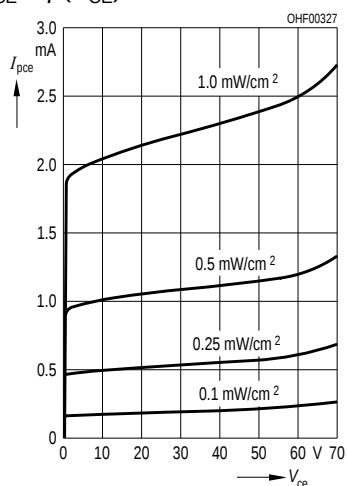
Total Power Dissipation

$$P_{\text{tot}} = f(T_A)$$



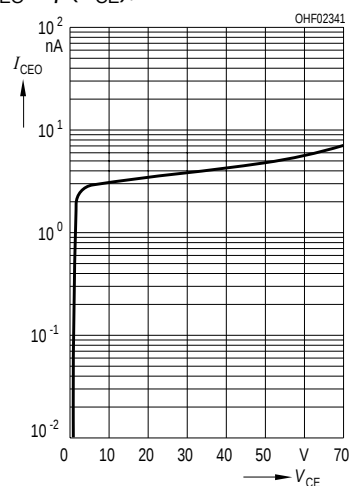
Photocurrent

$$I_{\text{PCE}} = f(V_{\text{CE}})$$

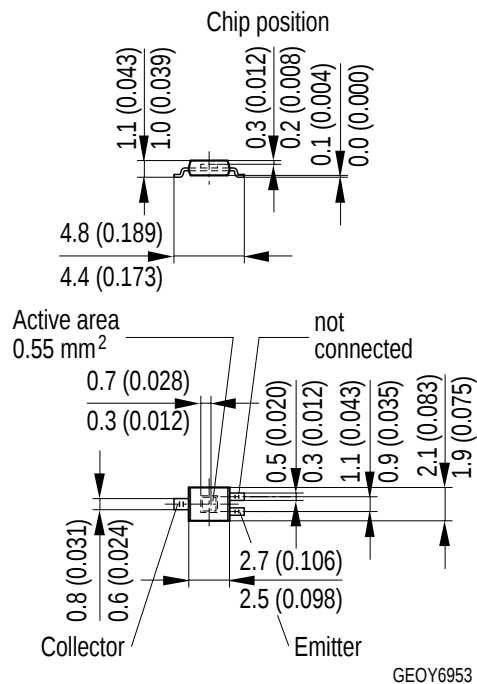


Dark Current

$$I_{\text{CEO}} = f(V_{\text{CE}}), E = 0$$



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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2001-12-11

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